

# LH2111/LH2311

## Dual Voltage Comparators

### General Description

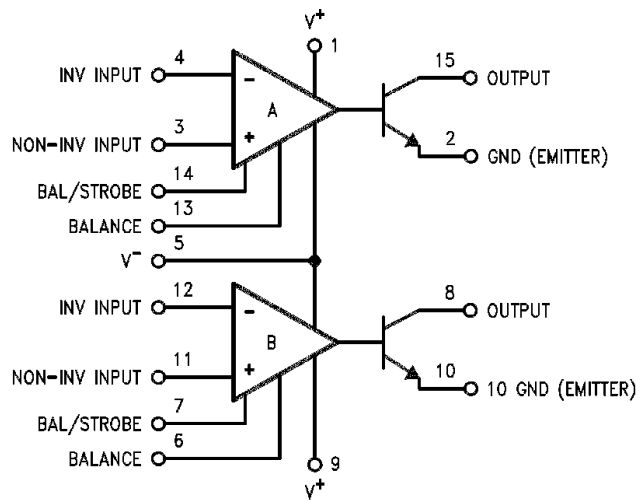
The LH2111 series of dual voltage comparators are two LM111 type comparators in a single hermetic package. Featuring all the same performance characteristics of the single, these duals offer in addition closer thermal tracking, lower weight, reduced insertion cost and smaller size than two singles. For additional information see the LM111 data sheet and National's Linear Application Handbook.

The LH2111 is specified for operation over the  $-55^{\circ}\text{C}$  to  $+125^{\circ}\text{C}$  military temperature range. The LH2311 is specified for operation over the  $0^{\circ}\text{C}$  to  $70^{\circ}\text{C}$  temperature range.

### Features

- Wide operating supply range  $\pm 15\text{V}$  to a single  $+5\text{V}$
- Low input currents  $6\text{ nA}$
- High sensitivity  $10\ \mu\text{V}$
- Wide differential input range  $\pm 30\text{V}$
- High output drive  $50\text{ mA}$ ,  $50\text{V}$

### Connection Diagram



DS010116-1

Order Number LH2111D, LH2111D/883 or LH2311D  
See NS Package Number D16C

## Absolute Maximum Ratings (Note \*NO TARGET FOR FNxref NS0050\*)

If Military/Aerospace specified devices are required, please contact the National Semiconductor Sales Office/ Distributors for availability and specifications.

Total Supply Voltage ( $V^+ - V^-$ )	36V
Output to Negative Supply Voltage ( $V_{OUT} - V^-$ )	50V
Ground to Negative Supply Voltage ( $GND - V^-$ )	30V
Differential Input Voltage	±30V

Input Voltage (Note 1)	±15V
Power Dissipation (Note 2)	500 mW
Output Short Circuit Duration	10 sec
Operating Temperature Range LH2111	-55°C to +125°C
LH2311	0°C to +70°C
Storage Temperature Range	-65°C to +150°C
Lead Temperature (Soldering, 10 sec)	300°C

## Electrical Characteristics (Note 3)

Each Side

Parameter	Conditions	Limits		Units
		LH2111	LH2311	
Input Offset Voltage (Note 4)	$T_A = 25^\circ\text{C}$ , $R_S \leq 50\text{k}$	3.0	7.5	mV Max
Input Offset Current (Note 4)	$T_A = 25^\circ\text{C}$	10	50	nA Max
Input Bias Current	$T_A = 25^\circ\text{C}$	100	250	nA Max
Voltage Gain	$T_A = 25^\circ\text{C}$	200	200	V/mV Typ
Response Time (Note 5)	$T_A = 25^\circ\text{C}$	200	200	ns Typ
Saturation Voltage	$V_{IN} \leq -5\text{ mV}$ , $I_{OUT} = 50\text{ mA}$ $T_A = 25^\circ\text{C}$	1.5	1.5	V Max
Strobe On Current	$T_A = 25^\circ\text{C}$	3.0	3.0	mA Typ
Output Leakage Current	$V_{IN} \geq 5\text{ mV}$ , $V_{OUT} = 35\text{V}$ $T_A = 25^\circ\text{C}$	10	50	nA Max
Input Offset Voltage (Note 4)	$R_S \leq 50\text{k}$	4.0	10	mV Max
Input Offset Current (Note 4)		20	70	nA Max
Input Bias Current		150	300	nA Max
Input Voltage Range		±14	±14	V Typ
Saturation Voltage	$V_+ \geq 4.5\text{V}$ , $V^- = 0$ $V_{IN} \leq -5\text{ mV}$ , $I_{SINK} \leq 8\text{ mA}$	0.4	0.4	V Max
Positive Supply Current	$T_A = 25^\circ\text{C}$	6.0	7.5	mA Max
Negative Supply Current	$T_A = 25^\circ\text{C}$	5.0	5.0	mA Max

**Note 1:** This rating applies for ±15V supplies. The positive input voltage limit is 30V above the negative supply. The negative input voltage limit is equal to the negative supply voltage or 30V below the positive supply, whichever is less.

**Note 2:** The maximum junction temperature is 150°C. For operating at elevated temperatures, devices in the flat package, the derating is based on a thermal resistance of 185°C/W when mounted on a 1/16-inch-thick epoxy glass board with 0.03-inch-wide, 2 ounce copper conductor. The thermal resistance of the dual-in-line package is 100°C/W, junction to ambient.

**Note 3:** These specifications apply for  $V_S = \pm 15\text{V}$  and  $-55^\circ\text{C} \leq T_A \leq 125^\circ\text{C}$  for the LH2111, and  $0^\circ\text{C} \leq T_A \leq 70^\circ\text{C}$  for the LH2311, unless otherwise stated. The offset voltage, offset current and bias current specifications apply for any supply voltage from a single 5V supply up to ±15V supplies. For the LH2311,  $V_{IN} = \pm 10\text{ mV}$ .

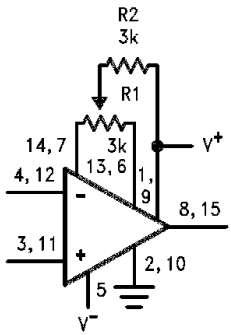
**Note 4:** The offset voltages and offset currents given are the maximum values required to drive the output within a volt of either supply with a 1 mA load. Thus, these parameters define an error band and take into account the worst case effects of voltage gain and input impedance.

**Note 5:** The response time specified is for a 100 mV input step with 5 mV overdrive.

**Note 6:** RETS2111X for the LH2111D and LH2111F military specifications.

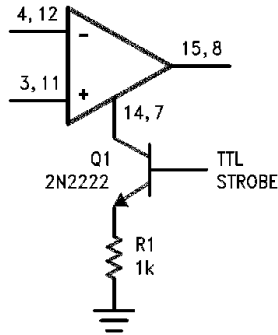
# Auxiliary Circuits

## Offset Balancing



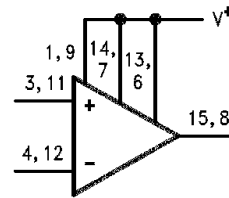
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## Strobing



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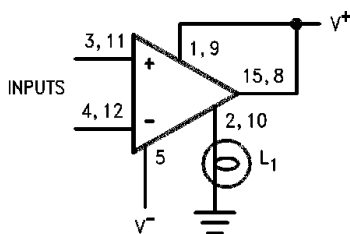
## Increasing Input Stage Current\*



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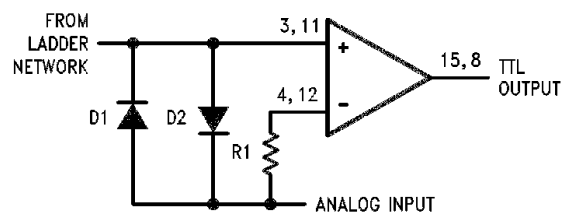
\*Increases typical common mode slew from 7.0 V/ $\mu$ s to 18 V/ $\mu$ s

## Driving Ground-Referred Load



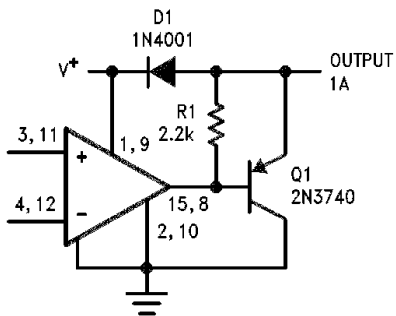
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## Using Clamp Diodes to Improve Responses



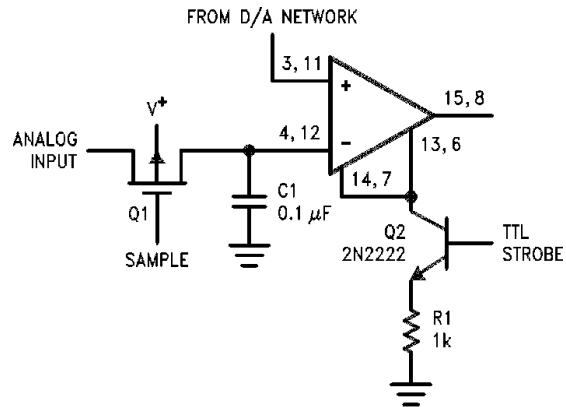
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## Comparator and Solenoid Driver



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## Strobing off Both Input\* and Output Stages

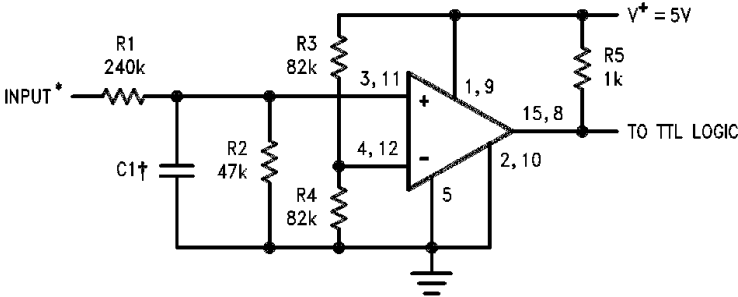


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\*Typical input current is 50 pA with inputs strobed off

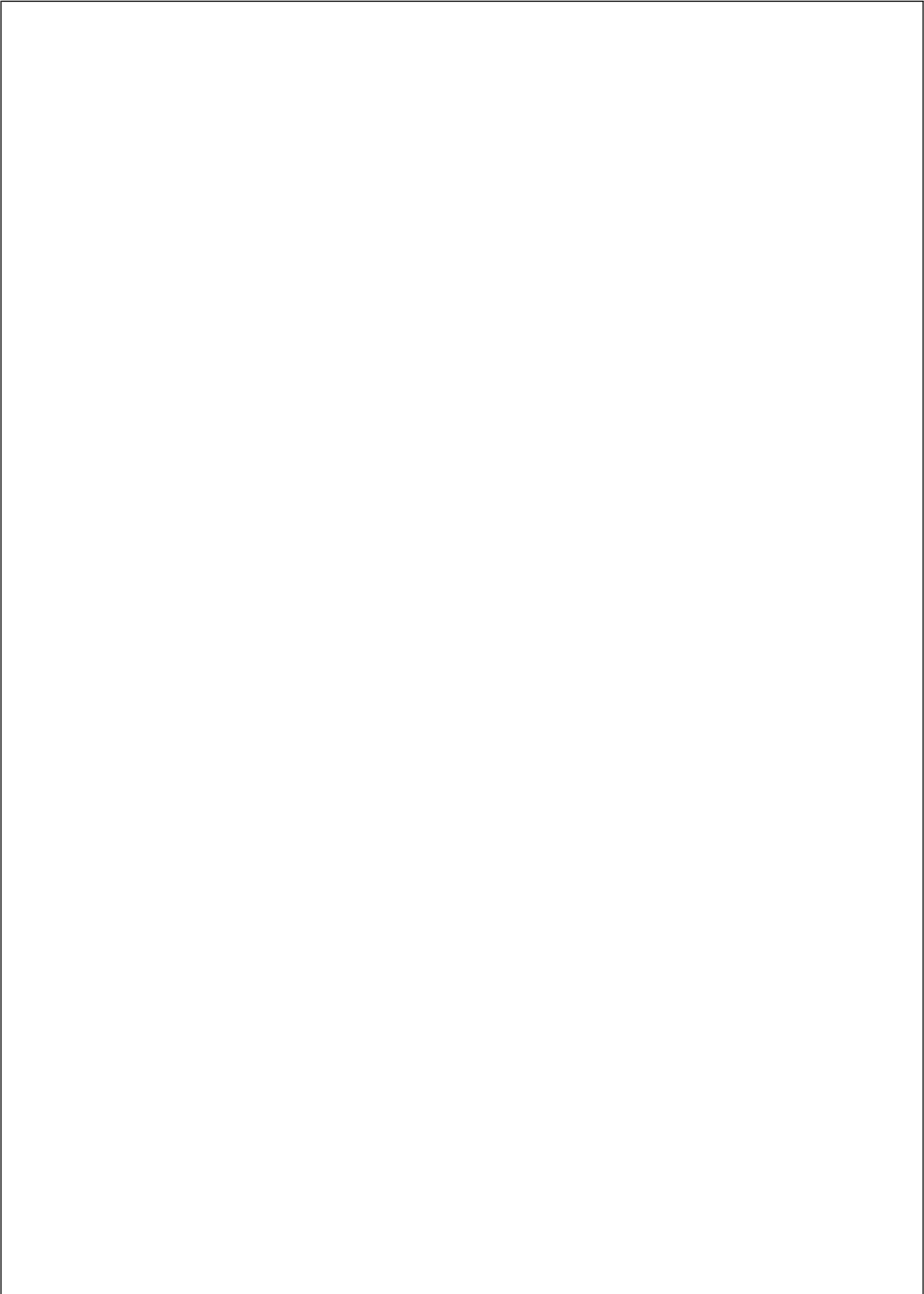
# Auxiliary Circuits (Continued)

### TTL Interface with High Level Logic

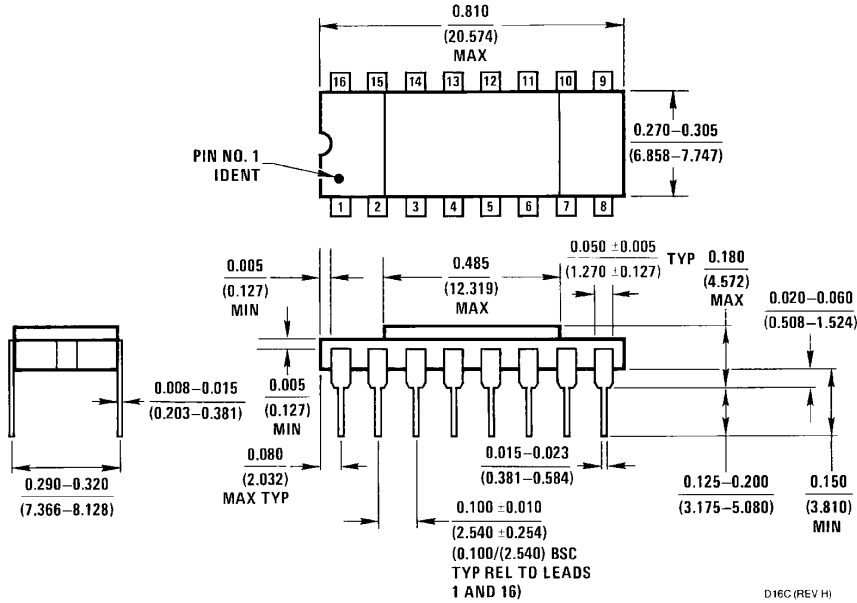


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\*Values shown are for a 0V to 30V logic swing and a 15V threshold.  
†May be added to control speed and reduce susceptibility to noise spikes.



**Physical Dimensions** inches (millimeters)



**16-Lead Hermetic Dual-In-Line Package (D)**  
**Order Number LH2111D, LH2111D/883 or LH2311D**  
**NS Package Number D16C**

D16C (REV H)

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**National Semiconductor Corporation**  
 1111 West Bardin Road  
 Arlington, TX 76017  
 Tel: 1(800) 272-9959  
 Fax: 1(800) 737-7018

www.national.com

**National Semiconductor Europe**

Fax: (+49) 0-180-530 85 86  
 Email: cnjwge@tevm2.nsc.com  
 Deutsch Tel: (+49) 0-180-530 85 85  
 English Tel: (+49) 0-180-532 78 32  
 Français Tel: (+49) 0-180-532 93 58  
 Italiano Tel: (+49) 0-180-534 16 80

**National Semiconductor Hong Kong Ltd.**

13th Floor, Straight Block,  
 Ocean Centre, 5 Canton Rd.  
 Tsimshatsui, Kowloon  
 Hong Kong  
 Tel: (852) 2737-1600  
 Fax: (852) 2736-9960

**National Semiconductor Japan Ltd.**

Tel: 81-043-299-2308  
 Fax: 81-043-299-2408